

SMALL SIGNAL NPN TRANSISTORS

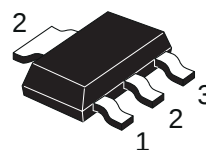
PRELIMINARY DATA

Type	Marking
BCP55	BCP55
BCP56	BCP56

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTORS
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE PNP COMPLEMENTARY TYPES ARE BCP52 AND BCP53 RESPECTIVELY

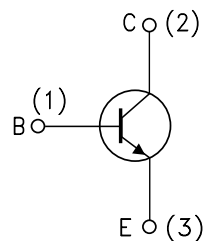
APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION



SOT-223

INTERNAL SCHEMATIC DIAGRAM



SC06960

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BCP55	BCP56	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	60	100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	60	80	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} = 1K\Omega$)	60	100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5		V
I_C	Collector Current	1		A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	1.5		A
I_B	Base Current	0.1		A
I_{BM}	Base Peak Current ($t_p <$ ms)	0.2		A
P_{tot}	Total Dissipation at $T_c = 25$ °C	2		W
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

BCP55 / BCP56

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	62.5	°C/W
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• Device mounted on a PCB area of 1 cm²

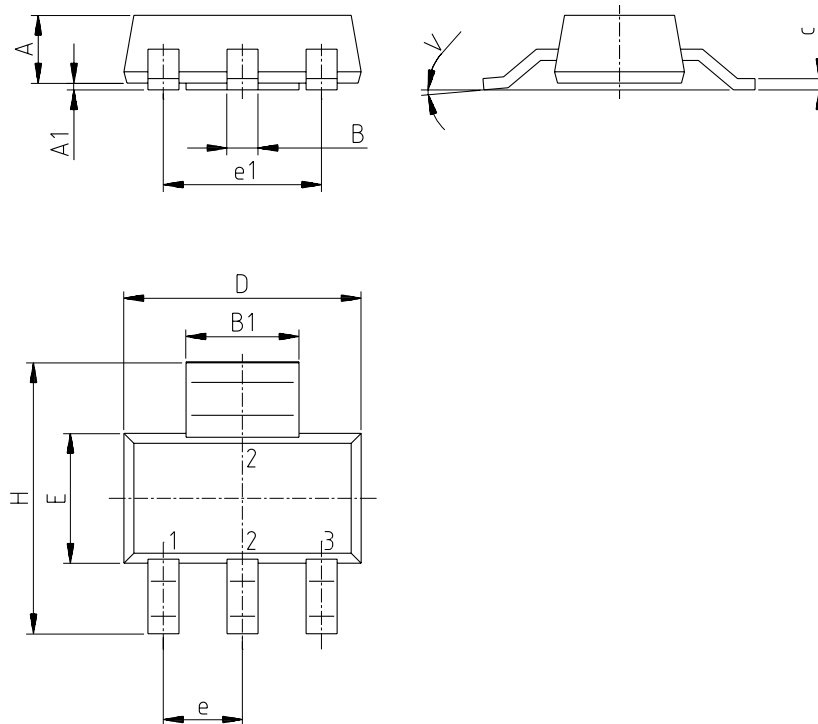
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 30 V V _{CB} = 30 V T _C = 125 °C			100 10	nA μA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = 100 μA for BCP55 for BCP56	60 100			V V
V _{(BR)CEO} *	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = 20 mA for BCP55 for BCP56	60 80			V V
V _{(BR)CER}	Collector-Emitter Breakdown Voltage (R _{BE} = 1 kΩ)	I _C = 100 μA for BCP55 for BCP56	60 100			V V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _C = 10 μA	5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 500 mA I _B = 50 mA			0.5	V
V _{BE(on)} *	Base-Emitter On Voltage	I _C = 500 mA V _{CE} = 2 V			1	V
h _{FE} *	DC Current Gain	I _C = 5 mA V _{CE} = 2 V I _C = 150 mA V _{CE} = 2 V for Gr. 16 I _C = 500 mA V _{CE} = 2 V	25 100 25		250	
f _T	Transition Frequency	I _C = 10 mA V _{CE} = 5 V f = 35 MHz		50		MHz

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1.5 %

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



P008B

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